

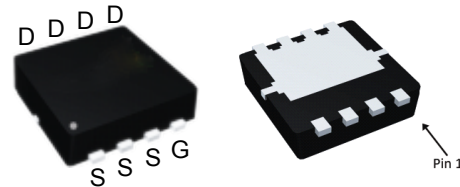
Features

- -60V/-17A,
 $R_{DS(ON)} = 32m\Omega(\text{typ.}) @ V_{GS} = -10V$
 $R_{DS(ON)} = 40m\Omega(\text{typ.}) @ V_{GS} = -4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- 100% UIS Tested

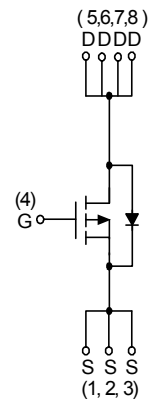
Applications

- DC/DC Converter.
- Power Management.
- Load Switch.

Pin Description



DFN3.3x3.3A-8_EP



P-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-60	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current		-17	A
I _{AS} ^a	Avalanche Current, Single pulse	L=0.5mH	-17	A
E _{AS} ^a	Avalanche Energy, Single pulse	L=0.5mH	72	mJ
I _{DP} ^b	Pulse Drain Current Tested	T _C =25°C	-80 ^c	A
I _D	Continuous Drain Current	T _C =25°C	-17	
		T _C =100°C	-6.8	
P _D	Maximum Power Dissipation	T _C =25°C	54	W
		T _C =100°C	21	
R _{θJC}	Thermal Resistance-Junction to Case		2.3	°C/W
I _D	Continuous Drain Current	T _A =25°C	-5.3	A
		T _A =70°C	-4.2	
P _D	Maximum Power Dissipation	T _A =25°C	2.2	W
		T _A =70°C	1.4	
R _{θJA} ^d	Thermal Resistance-Junction to Ambient	Steady State	55	°C/W

Note a : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

Note b : Pulse width limited by max. junction temperature.

Note c : Wire limited.

Note d : $R_{\theta JA}$ steady state $t=999\text{s}$. $R_{\theta JA}$ is measured with the device mounted on 1in^2 , FR-4 board with 2oz. Copper.

Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

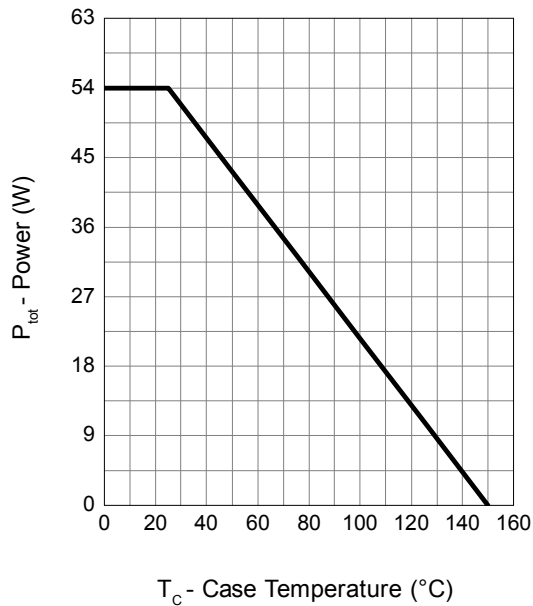
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-48V, V _{GS} =0V T _J =85°C	-	-	1 -30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.3	-1.8	-2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^e	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-20A V _{GS} =-4.5V, I _{DS} =-20A	-	32 40	40 54	mΩ mΩ
Diode Characteristics						
V _{SD} ^e	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.7	-1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-20A, dI _{SD} /dt=100A/μs	-	23	-	ns
Q _{rr}	Reverse Recovery Charge		-	22	-	nC
Dynamic Characteristics ^f						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	8	16	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, Frequency=1.0MHz	-	2200	2540	pF
C _{oss}	Output Capacitance		-	842	-	
C _{rss}	Reverse Transfer Capacitance		-	95	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-30V, R _L =30Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	10	18	ns
t _r	Turn-on Rise Time		-	9	16	
t _{d(OFF)}	Turn-off Delay Time		-	88	158	
t _f	Turn-off Fall Time		-	42	76	
Gate Charge Characteristics ^f						
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-10V, I _{DS} =-20A	-	32	45	nC
Q _{gs}	Gate-Source Charge		-	3.6	-	
Q _{gd}	Gate-Drain Charge		-	8.3	-	

Note e : Pulse test; pulse width≤300μs, duty cycle≤2%.

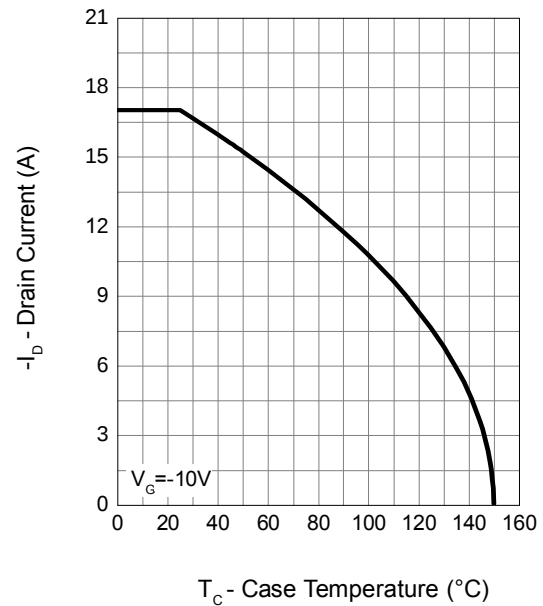
Note f : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

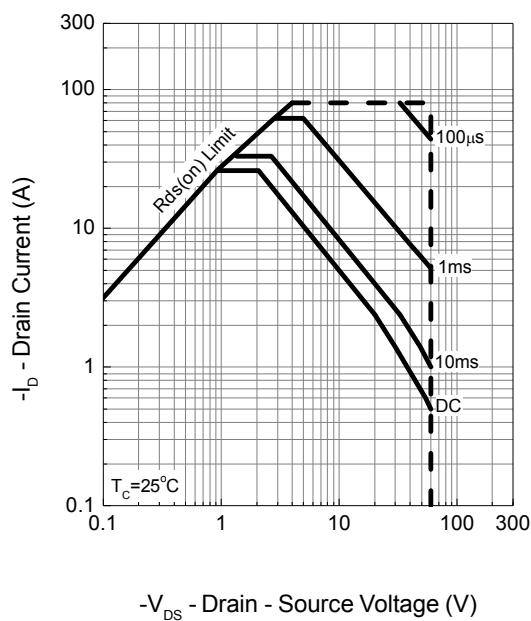
Power Dissipation



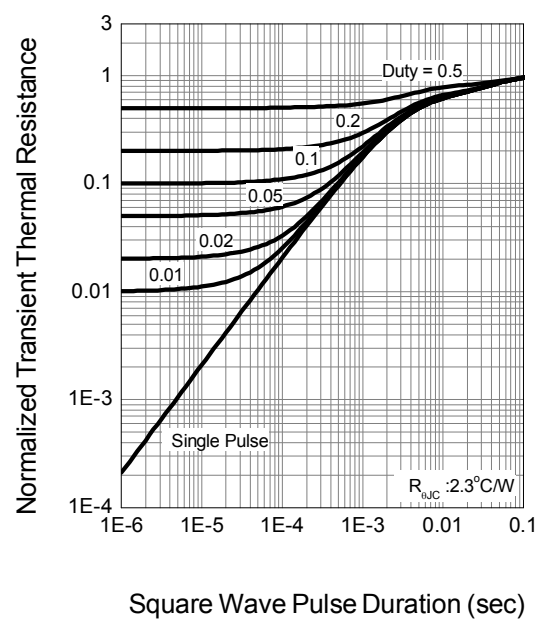
Drain Current



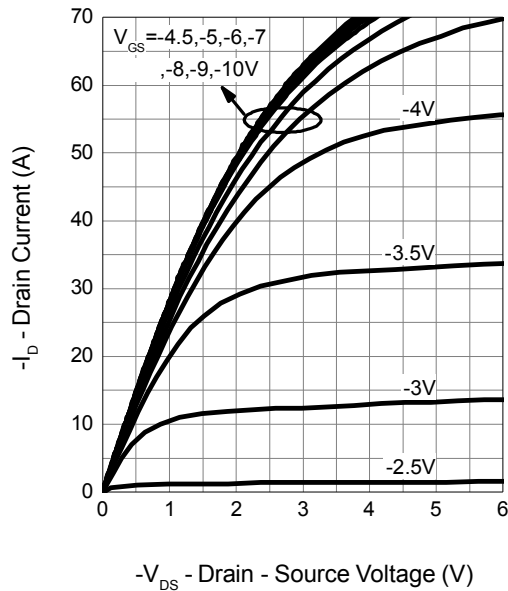
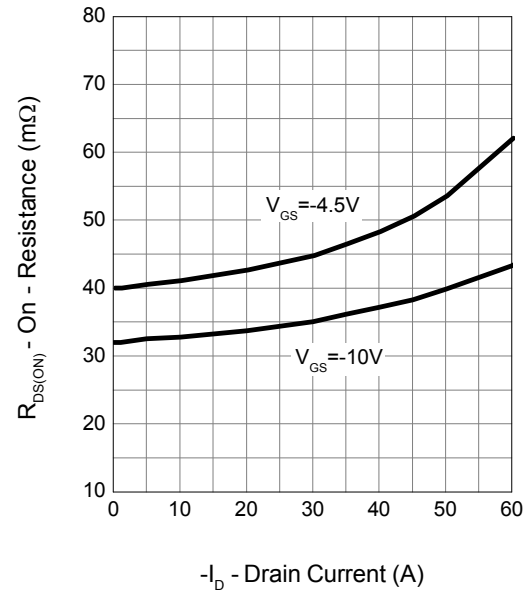
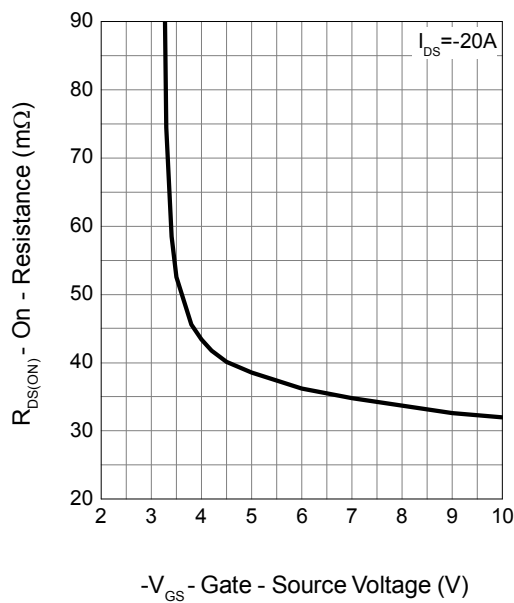
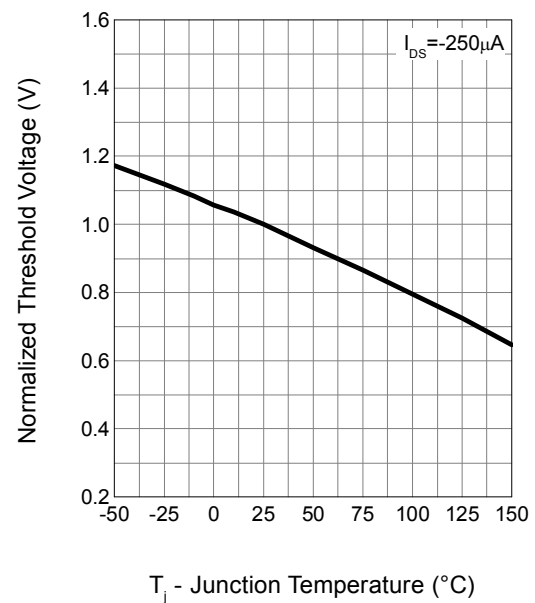
Safe Operation Area



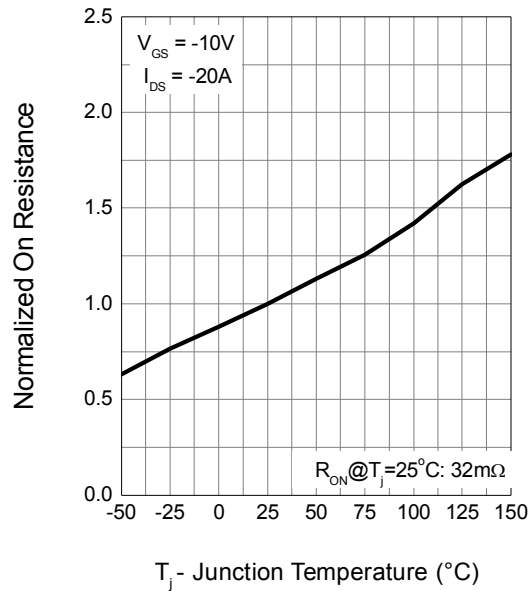
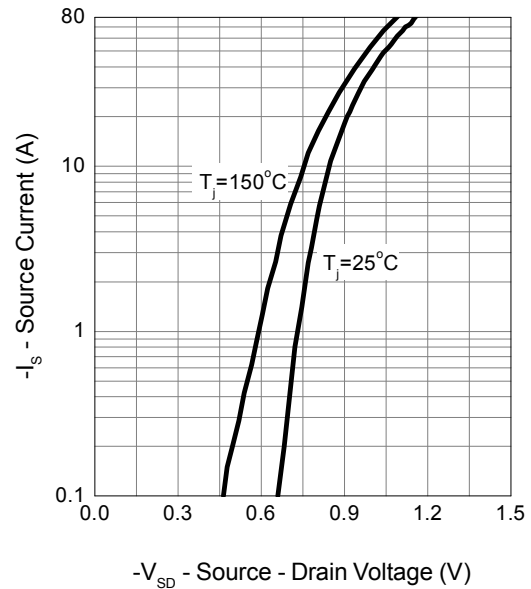
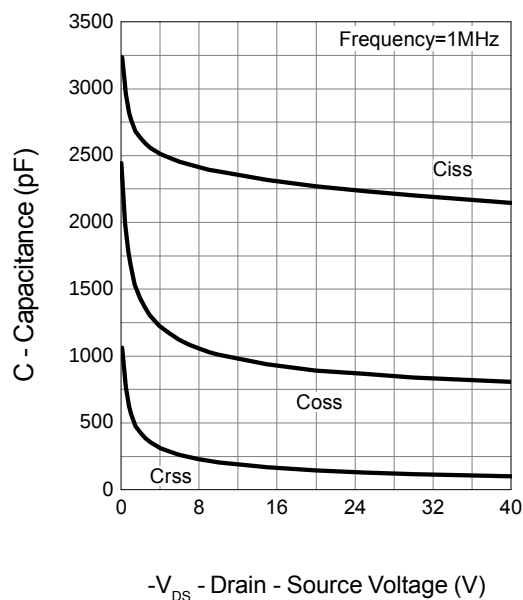
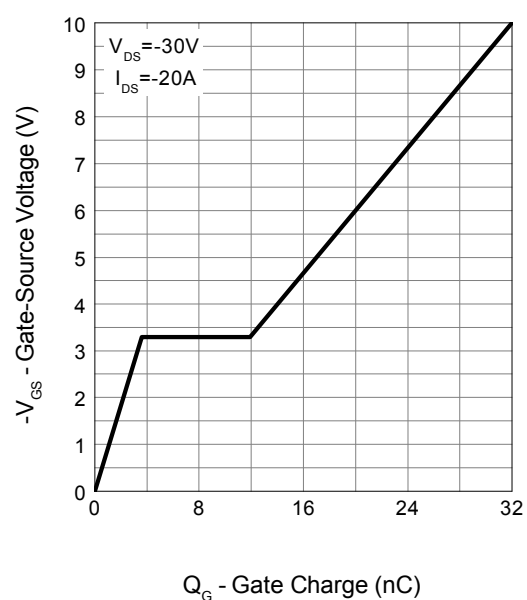
Thermal Transient Impedance



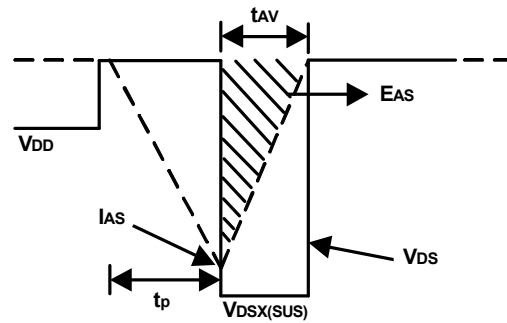
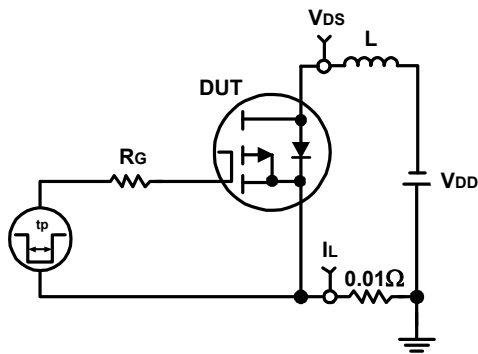
Typical Operating Characteristics (Cont.)

Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


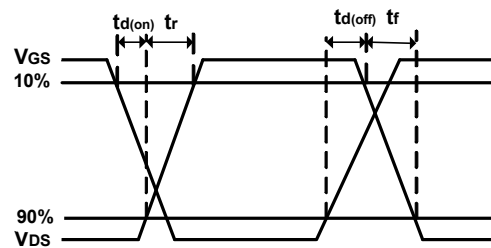
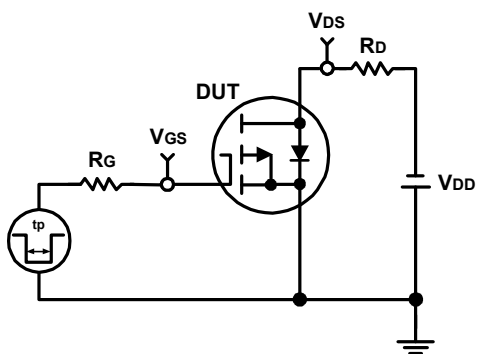
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance

Source-Drain Diode Forward

Capacitance

Gate Charge


Avalanche Test Circuit and Waveforms

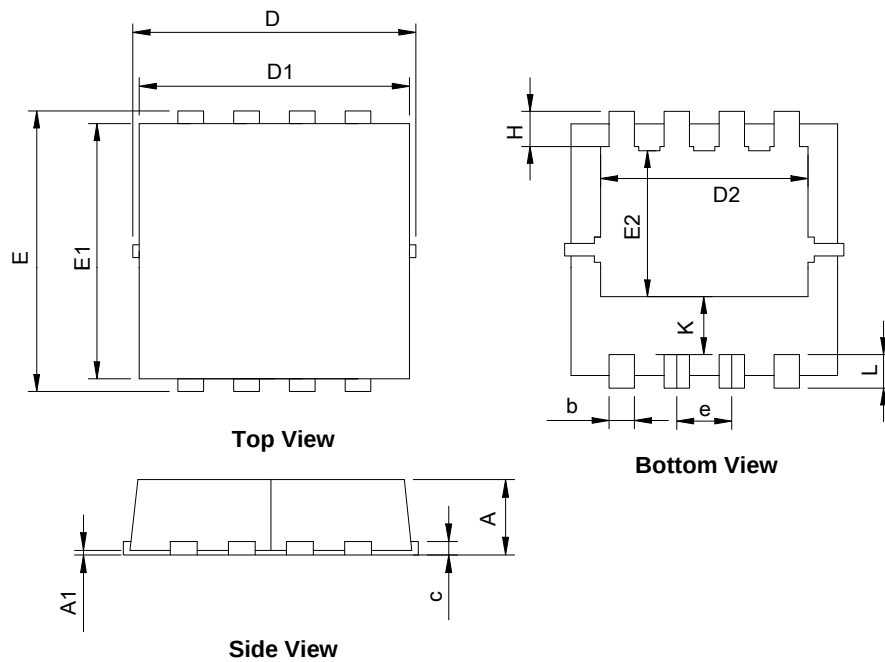


Switching Time Test Circuit and Waveforms



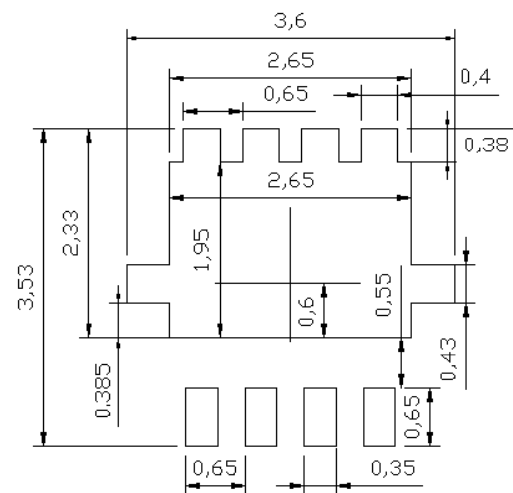
Package Information

DFN3.3x3.3A-8_EP1_P



SYMBOL	DFN3.3x3.3A-8_EP1_P			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.10	0.25	0.004	0.010
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.59	0.093	0.102
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.98	0.065	0.078
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm